

IN THE CLAIMS:

Please amend claim 8 as follows:

1. (Previously Presented) A method for manufacturing a liquid crystal panel of an active matrix system, comprising the steps of:

performing arraying for plotting a master glass substrate into a plurality of blocks, further plotting each block into at least one device-forming region, and forming a conductive film, an insulating film and a semiconductor film which constitute TFT (Thin Film Transistor) in the device-forming region;

performing primary cutting for cutting the master glass substrate into the respective blocks to form a plurality of sub-TFT substrates;

performing sub-TFT substrate processing for executing processing for each sub-TFT substrate in accordance with a device to be manufactured; and

performing secondary cutting for cutting the sub-TFT substrate into the device-forming regions,

wherein said sub-TFT substrate processing step includes a step of forming a semiconductor film above the sub-TFT substrate.

2. (Original) A manufacturing method of a liquid crystal panel according to claim 1, wherein only liquid crystal panels having identical sizes are formed in each block of the master glass substrate.

3. (Previously Presented) A manufacturing method of a liquid crystal panel according to claim 1, wherein at least two kinds of liquid crystal panels different from each other in size are formed in each block of the master glass substrate.

4. (Previously Presented) A method for manufacturing a liquid crystal panel of an active matrix system, comprising the steps of:

performing arraying for plotting a master glass substrate into a plurality of blocks, further plotting each block into at least one device-forming region, and forming a conductive film, an insulating film and a semiconductor film which constitute TFT (Thin Film Transistor) in the device-forming region;

performing primary cutting for cutting the master glass substrate into the respective blocks to form a plurality of sub-TFT substrates;

performing sub-TFT substrate processing for executing processing for each sub-TFT substrate in accordance with a device to be manufactured; and

performing secondary cutting for cutting the sub-TFT substrate into the device-forming regions, wherein said sub-TFT substrate processing step further includes the steps of:

forming a pixel electrode above the sub-TFT substrate; and
joining a second substrate onto the sub-TFT substrate; and
after the secondary cutting step, a step of sealing a liquid crystal between the sub-TFT substrate and the second substrate after the cutting is provided.

5. (Original) A manufacturing method of a liquid crystal panel according to claim 1, wherein said arraying step includes the steps of: forming an amorphous silicon film above the master glass substrate; and converting the amorphous silicon film into a polysilicon film by irradiating the amorphous silicon film with a rectangular laser beam and moving the laser beam in one direction.

6. (Previously Presented) A manufacturing method of a liquid crystal panel according to claim 1, wherein said sub-TFT substrate processing step further includes at least one of the steps of:

performing corner cutting for the sub-TFT substrate after the primary cutting; and
performing end face processing for the sub-TFT substrate after the primary cutting.

7. (Previously Presented) A manufacturing method of a liquid crystal panel according to claim 1, wherein, when plotting each block into said at least one device-forming region, the device-forming region is plotted to include a display section and a driving section of a liquid crystal panel having a united driving circuit, where an extending direction of the driving section with respect of the display section is substantially identical among each of the blocks.

8. (Currently Amended) A method for manufacturing a liquid crystal panel of an active matrix system, comprising the steps of:

performing arraying for plotting a master glass substrate into a plurality of blocks, further plotting each block into at least one device-forming region, and forming a conductive film, an insulating film and a semiconductor film which constitute TFT (Thin Film Transistor) in the device-forming region;

performing primary cutting for cutting the master glass substrate into the respective blocks to form a plurality of sub-TFT substrates;

performing sub-TFT substrate processing for executing processing for each sub-TFT substrate in accordance with a device to be manufactured; and

performing secondary cutting for cutting the sub-TFT substrate into the device-forming regions, wherein further in said sub-TFT substrate processing step, pattern alignment is performed by fusing providing a fiducial mark provided for on each sub-TFT substrate.

9. (Canceled)

10. (Previously Presented) A manufacturing method of a liquid crystal panel according to claim 1, wherein in at least one of the plurality of blocks, a photoelectric conversion element using the semiconductor film is formed.

11. (Previously Presented) A manufacturing method of a liquid crystal panel according to claim 1, wherein direct-vision liquid crystal panels are formed in said at least one device-forming region.

12. (Previously Presented) A manufacturing method of a liquid crystal panel according to claim 1, wherein direct-vision liquid crystal panels are formed in said at least one device-forming region, and a projection panel type is formed in another device-forming region.

13. (Previously Presented) A manufacturing method of a liquid crystal panel according to claim 1, wherein a liquid crystal panel of a transmission type is formed in a part of said at least one device-forming region, and a projection panel of a reflection type is formed in another device-forming region.

14. (Previously Presented) A manufacturing method of a liquid crystal panel according to claim 1, wherein in one of said at least one device-forming region, a liquid crystal panel with a built-in image sensor is formed.

15-17. (Canceled)